

# InGaAs PIN photodiode with preamp G8339/G8342/G7881/G8796 series

Receptacle type, 1.3/1.55  $\mu\text{m}$ , 156, 622 Mbps/1.25, 2.5 Gbps



G8339/G8342/G7881/G8796 series are high-speed receivers specifically developed for 1.3/1.55  $\mu\text{m}$  band optical fiber communications. These devices incorporate a high-speed, high-sensitivity InGaAs PIN photodiode and a high-speed preamp integrated in a receptacle module. Packages are available with various connectors and mounting styles.

## Features

- Wide dynamic range  
G8339 series (156 Mbps) : -37 to -5 dBm  
G8342 series (622 Mbps) : -32 to -5 dBm  
G7881 series (1.25 Gbps) : -25 to -1 dBm  
G8796 series (2.5 Gbps) : -22 to +1 dBm
- Integrated with trans-impedance amplifier
- Supply voltage  
G8339/G8342 series: 3.3 V  
G7881/G8796 series: 3.3 V, 5 V
- Differential output

## Applications

- Optical fiber communications
- Fiber channel
- Gigabit Ethernet
- HDTV
- SDH

### ■ Absolute maximum ratings (Ta=25 °C)

| Parameter             | Symbol           | G8339 series | G8342 series | G7881 series | G8796 series | Unit |
|-----------------------|------------------|--------------|--------------|--------------|--------------|------|
| Supply voltage        | Vcc              | -0.3, +3.8   | -0.3, +3.8   | -0.3, +5.5   | -0.5, +6     | V    |
| Operating temperature | T <sub>opr</sub> | -20 to +70   |              |              |              | °C   |
| Storage temperature   | T <sub>stg</sub> | -40 to +85   |              |              |              | °C   |

### ■ Specifications (Typ. Ta=25 °C, V<sub>ee</sub>=0 V, capacitive coupling, $\lambda$ =1.31 $\mu\text{m}$ , unless otherwise noted)

| Parameter           | Symbol          | Condition                             | G8339 series                                              | G8342 series                                              | G7881 series                                            | G8796 series                                            | Unit |
|---------------------|-----------------|---------------------------------------|-----------------------------------------------------------|-----------------------------------------------------------|---------------------------------------------------------|---------------------------------------------------------|------|
|                     |                 |                                       | V <sub>cc</sub> =3.3 V<br>R <sub>L</sub> =500 $\Omega$ *1 | V <sub>cc</sub> =3.3 V<br>R <sub>L</sub> =500 $\Omega$ *1 | V <sub>cc</sub> =3.3/5 V<br>R <sub>L</sub> =50 $\Omega$ | V <sub>cc</sub> =3.3/5 V<br>R <sub>L</sub> =50 $\Omega$ |      |
| Photo sensitivity   | S               | *2, *3                                | 27                                                        | 17                                                        | 2.8                                                     | 1.2                                                     | V/mW |
| Supply current      | I <sub>cc</sub> | dark state, R <sub>L</sub> = $\infty$ | 25                                                        | 30                                                        | 35                                                      | 35                                                      | mA   |
| Output bias voltage | V <sub>o</sub>  | dark state, R <sub>L</sub> = $\infty$ | 1.5                                                       | 1.65                                                      | V <sub>cc</sub> - 1.7                                   | V <sub>cc</sub> - 0.25                                  | V    |
| Rise time           | t <sub>r</sub>  | *3, 20 to 80 %                        | 2000                                                      | 500                                                       | 250                                                     | 150                                                     | ps   |
| Data rate           | B               |                                       | 156 M                                                     | 622 M                                                     | 1.25 G                                                  | 2.5 G                                                   | bps  |

\*1: G8339/G8342 series cannot be operated with R<sub>L</sub>=50  $\Omega$ , so they should be used with a load resistance larger than 500  $\Omega$ .

\*2: Single ended (V<sub>out</sub>+) measurement using a single mode optical fiber with a master plug.

\*3: G8339/G8342 series: Pin= -30 dBm

G7881 series: Pin= -22 dBm

G8796 series: Pin= -17 dBm

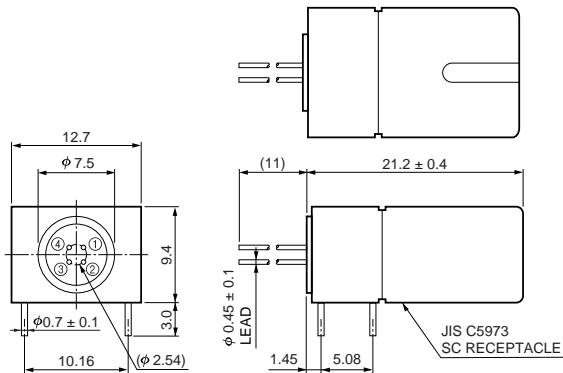
### ■ Package lineup

| Parameter           | G8339/G8342/G7881/G8796 |     |     |       |               |
|---------------------|-------------------------|-----|-----|-------|---------------|
|                     | -21                     | -22 | -23 | -32   | -44           |
| Mounting style      | Board                   |     |     | Panel | Board & panel |
| Connector           | SC                      | FC  | MU  | FC    | LC            |
| Dimensional outline | ①                       | ②   | ③   | ④     | ⑤             |

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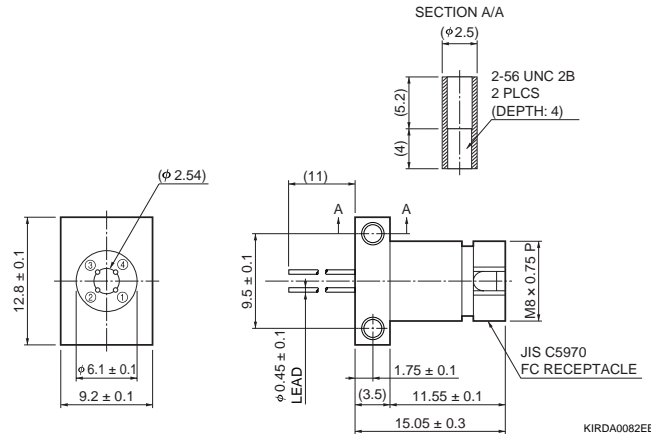
■ Dimensional outlines (unit: mm, tolerance unless otherwise noted:  $\pm 0.2$  mm)

① G8339/G8342/G7881/G8796-21



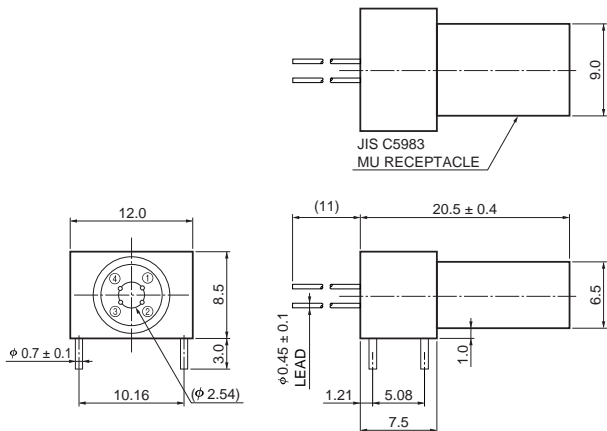
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② G8339/G8342/G7881/G8796-22



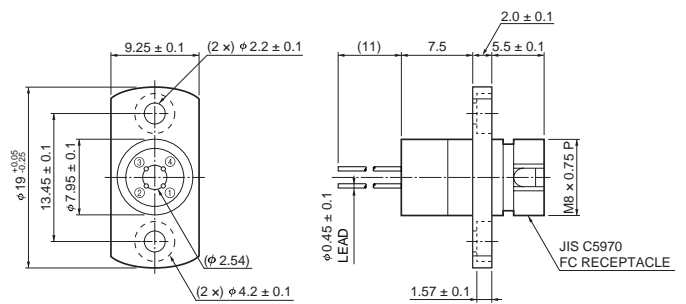
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③ G8339/G8342/G7881/G8796-23



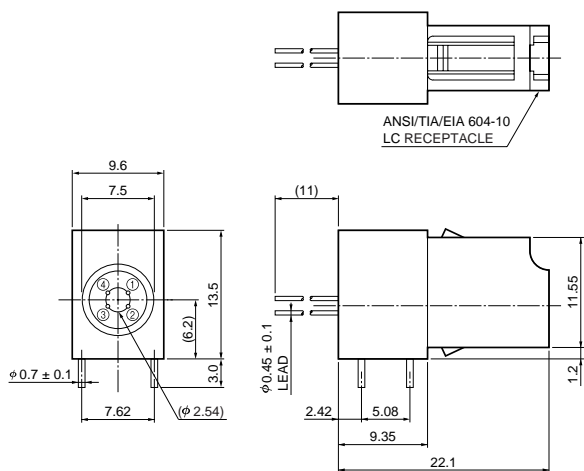
KIRDA0109EA

④ G8339/G8342/G7881/G8796-32



KIRDA0083EB

⑤ G8339/G8342/G7881/G8796-44



KIRDA0110EB

## ■ Pin connection

| Pin No. | G8339/G8342/<br>G8796 Series | G7881 Series |
|---------|------------------------------|--------------|
| ①       | Vcc                          | Vcc          |
| ②       | Vout -                       | Vout +       |
| ③       | Vee                          | Vee          |
| ④       | Vout +                       | Vout -       |

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Cat. No. KIRD1030E04  
Jan. 2002 DN